

1. Scope :

This specification applies to P/N silicon zener diode chips,
Device NO. SD-30660G

2. Structure :

- 2-1. Planar type : P/N Diode
- 2-2. Electrodes :
Top side : Gold pad.
Back side : Gold layer.

3. Size :

- 3-1. ^{**1} Chip size : 6.88 mils x 6.88 mils (0.175 mm x 0.175 mm).
 - 3-2. Chip thickness : 3.3 ± 0.6 mils (0.085 ± 0.015 mm)
 - 3-3. Active area : 4.1 mils x 4.1 mils (0.105 mm x 0.105 mm).
 - 3-4. ^{**2} Bonding pad : 4.8 mils x 4.8 mils (0.122 mm x 0.122 mm).
 - 3-5. Pattern drawing : Refer to the attached drawing.
- ^{**1} Including scribing line. The chip size is about $(0.150 \pm 0.015)^2 \text{mm}^2$ after dicing.
^{**2} The bonding pad dimension is $(0.122 \pm 0.005)^2 \text{mm}^2$.

4. Electrical characteristics (Ta = 25 °C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse Leakage Current	I _R	V _R =4V Ee=0mW/cm ²			100	nA
		V _R =5V Ee=0mW/cm ²			0.5	μA
Zener Voltage	V _Z	I _Z =5mA Ee=0mW/cm ²	5.8		6.8	V
Forward Voltage	V _f	I _F =20mA Ee=0mW/cm ²			1.2	V

